



YEA SHIN TECHNOLOGY CO., LTD

YS3912Q

N-Channel Enhancement MOSFET



VDS= 30V, ID= 6.5A

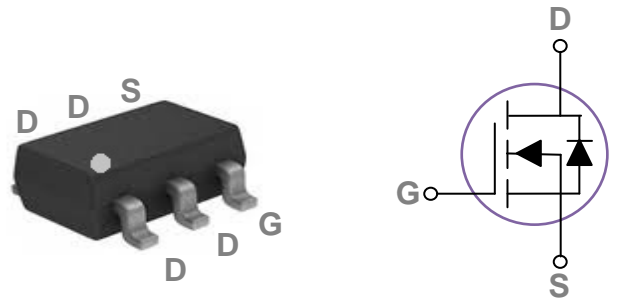
Features

- 30V, 6.5A, $R_{DS(ON)} = 24m\Omega @ V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

Applications

- MB / VGA / Vcore
- Load Switch
- Hand-Held Instrument

SOT-26 Configuration



Absolute Maximum Rating $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous ($T_c=25^\circ C$)	6.5	A
	Drain Current – Continuous ($T_c=100^\circ C$)	4.1	A
I _{DM}	Drain Current – Pulsed ¹	26	A
EAS	Single Pulse Avalanche Energy ²	32	mJ
IAS	Single Pulse Avalanche Current ²	8	A
P _D	Power Dissipation ($T_c=25^\circ C$)	1.56	W
	Power Dissipation – Derate above 25 $^\circ C$	0.012	W/ $^\circ C$
T _{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T _J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	80	$^\circ C/W$

DEVICE CHARACTERISTICS

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.04	---	$V/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-source On-Resistance ³	$V_{GS}=10V, I_D=6A$	---	19	24	$m\Omega$
		$V_{GS}=4.5V, I_D=4A$	---	25	34	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.6	2.2	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4	---	$mV/^\circ\text{C}$
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=4A$	---	6.5	---	S

Dynamic and Switching Characteristics

Q_g	Total Gate Charge ^{3,4}	$V_{DS}=15V, V_{GS}=4.5V, I_D=6A$	---	4.1	8	nC
Q_{gs}	Gate-Source Charge ^{3,4}		---	1	2	
Q_{gd}	Gate-Drain Charge ^{3,4}		---	2.1	4	
$T_{d(on)}$	Turn-On Delay Time ^{3,4}	$V_{DD}=15V, V_{GS}=10V, R_G=6\Omega, I_D=1A$	---	2.8	5	ns
T_r	Rise Time ^{3,4}		---	7.2	14	
$T_{d(off)}$	Turn-Off Delay Time ^{3,4}		---	15.8	30	
T_f	Fall Time ^{3,4}		---	4.6	9	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	345	500	pF
C_{oss}	Output Capacitance		---	55	80	
C_{rss}	Reverse Transfer Capacitance		---	32	45	
R_g	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, f=1\text{MHz}$	---	3.2	6.4	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	6.5	A
I_{SM}	Pulsed Source Current ³		---	---	26	A
V_{SD}	Diode Forward Voltage ³	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=25V, V_{GS}=10V, L=1\text{mH}, I_{AS}=8A, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$.
3. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

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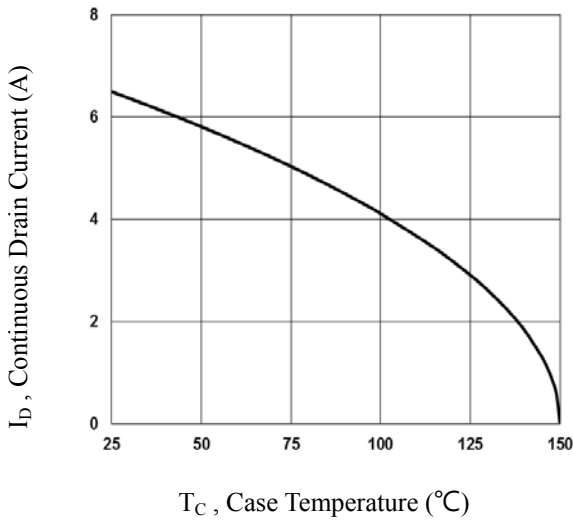


Fig.1 Continuous Drain Current vs. T_C

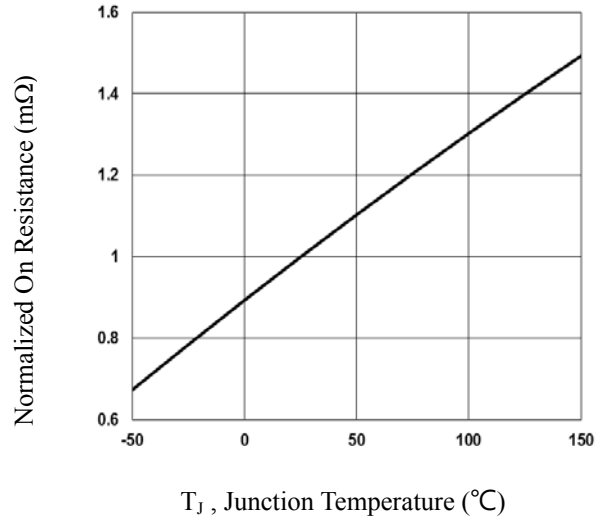


Fig.2 Normalized RDSON vs. T_J

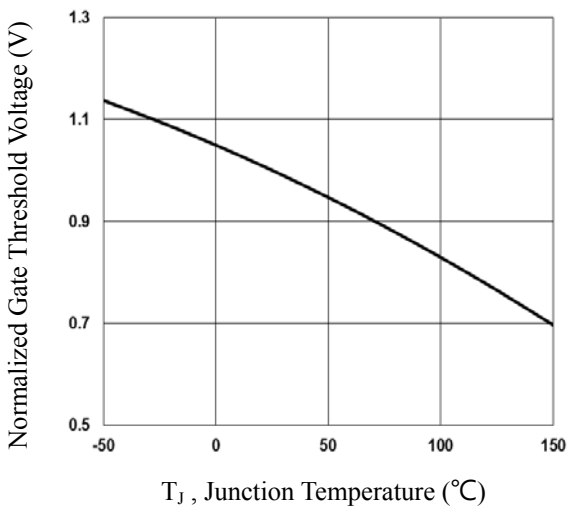


Fig.3 Normalized V_{th} vs. T_J

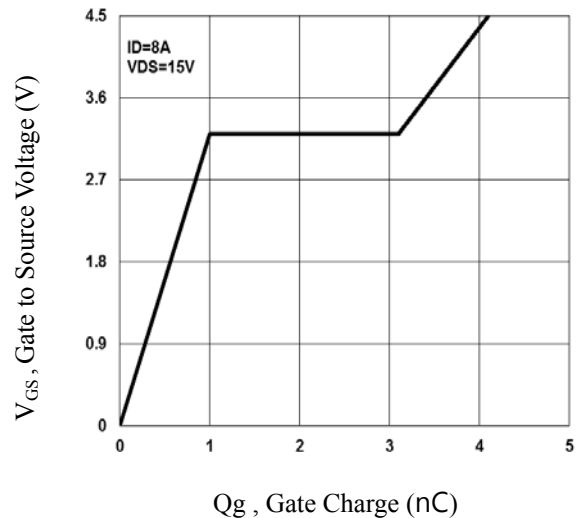


Fig.4 Gate Charge Waveform

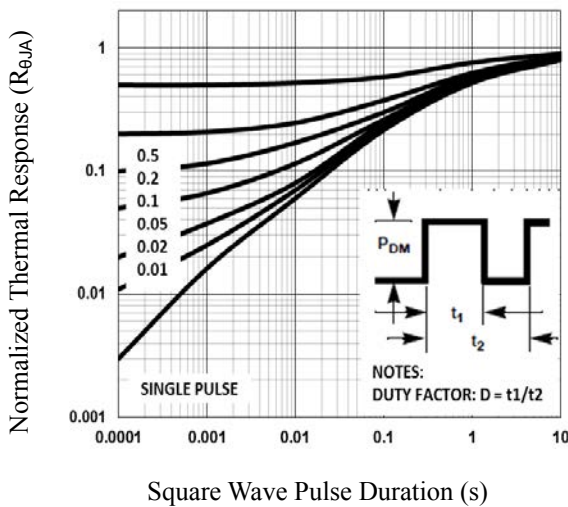


Fig.5 Normalized Transient Impedance

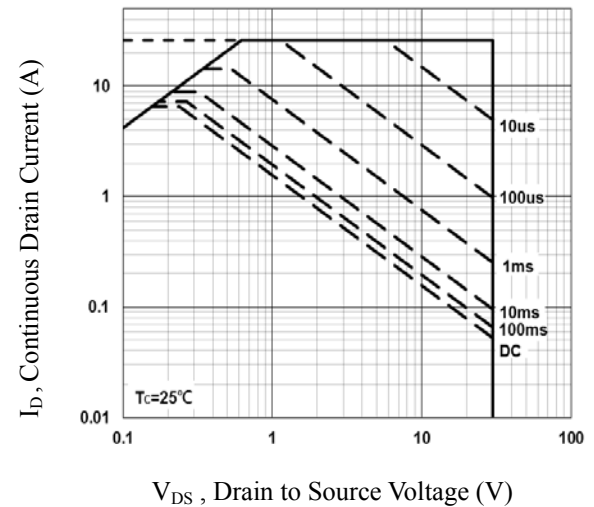


Fig.6 Maximum Safe Operation Area

DEVICE CHARACTERISTICS

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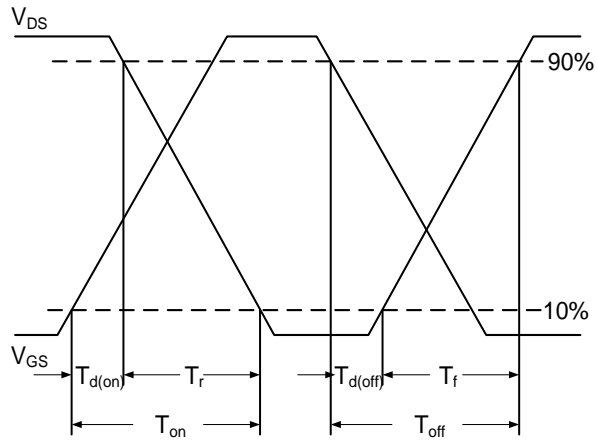


Fig.7 Switching Time Waveform

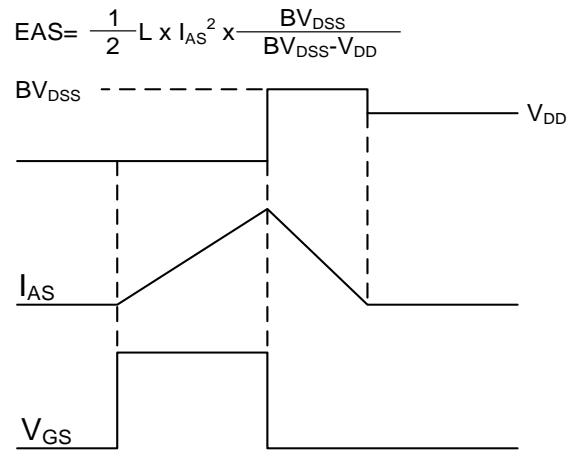
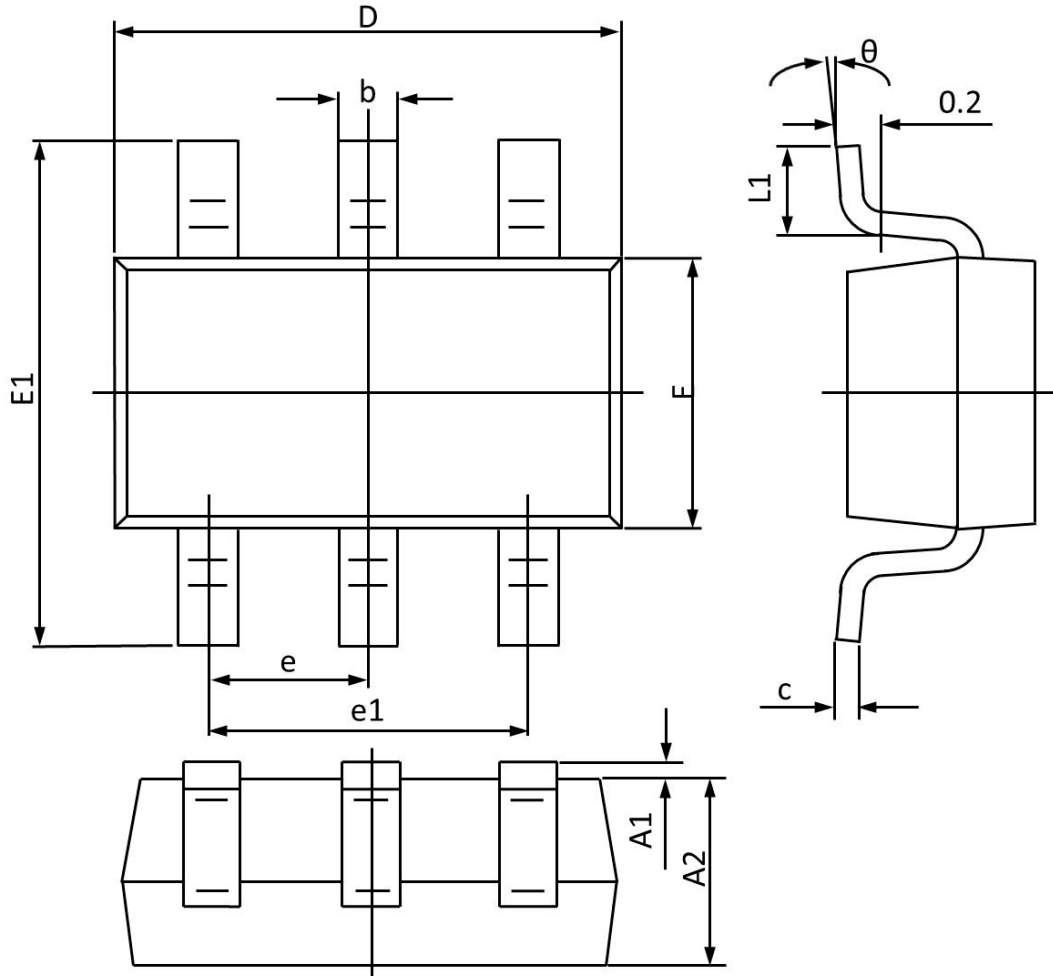


Fig.8 EAS Waveform

PACKAGE OUTLINE & DIMENSIONS

YS3912Q

SOT-26 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A1	0.000	0.100	0.000	0.004
A2	1.000	1.200	0.040	0.047
b	0.300	0.500	0.012	0.019
c	0.047	0.207	0.002	0.008
D	2.800	3.000	0.110	0.118
E1	2.600	3.000	0.103	0.118
e	0.950 TYP		0.037 TYP	
e1	1.900 TYP		0.075 TYP	
L1	0.250	0.550	0.010	0.021
θ	0°	8°	0°	8°